

DB101 THRU DB107

Features

- Through Hole Package
- Glass Passivated Diode Construction
- Moisture Resistant Epoxy Case
- High Surge Current Capability

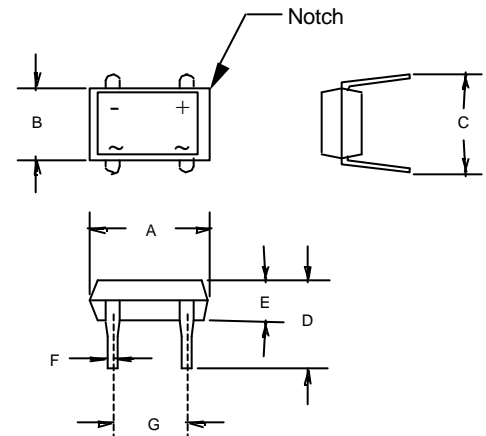
**1 Amp Single Phase
Glass Passivated
Bridge Rectifier
50 to 1000 Volts**

Maximum Ratings

- Operating Junction Temperature: -55°C to +125°C
- Storage Temperature: -55°C to +150°C

MCC Catalog Number	Device Marking	Maximum Recurrent Peak Reverse Voltage	Maximum RMS Voltage	Maximum DC Blocking Voltage
DB101	DB101	50V	35V	50V
DB102	DB102	100V	70V	100V
DB103	DB103	200V	140V	200V
DB104	DB104	400V	280V	400V
DB105	DB105	600V	420V	600V
DB106	DB106	800V	560V	800V
DB107	DB107	1000V	700V	1000V

DB-1



Electrical Characteristics @ 25°C Unless Otherwise Specified

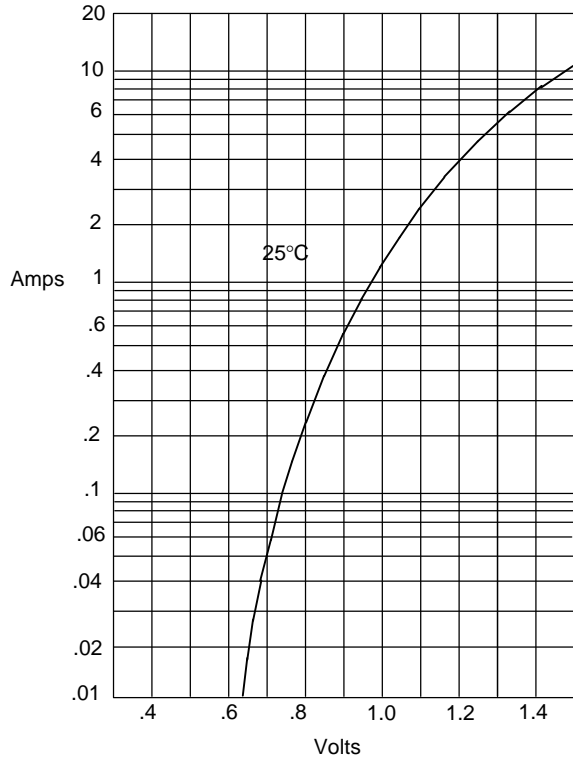
Average Forward Current	$I_{F(AV)}$	1 A	$T_A = 40^\circ\text{C}$
Peak Forward Surge Current	I_{FSM}	50A	8.3ms, half sine
Maximum Instantaneous Forward Voltage	V_F	1.1V	$I_{FM} = 1.0\text{A};$ $T_J = 25^\circ\text{C}$
Maximum DC Reverse Current At Rated DC Blocking Voltage	I_R	10μA 0.5mA	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$
Typical Junction Capacitance	C_J	25pF	Measured at 1.0MHz, $V_R=4.0\text{V}$

*Pulse Test: Pulse Width 300μsec, Duty Cycle 2%

DIM	DIMENSIONS				NOTE
	INCHES		MM		
	MIN	MAX	MIN	MAX	
A	.320	.335	8.13	8.51	
B	.245	.255	6.20	6.50	
C	.300	.350	7.60	8.90	
D	.236	.283	6.01	7.20	
E	.120	.130	3.05	3.30	
F	.016	.022	0.41	0.56	
G	.195	.205	5.00	5.20	

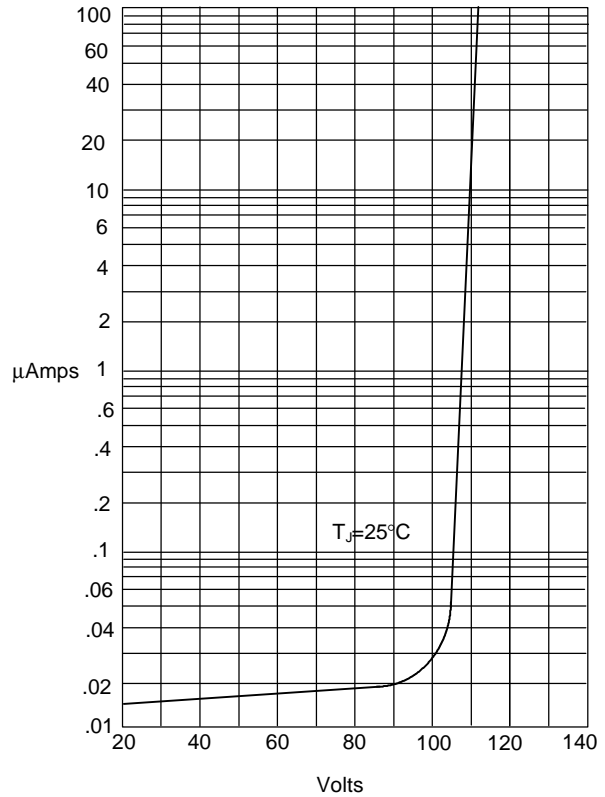
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Figure 1
Typical Forward Characteristics



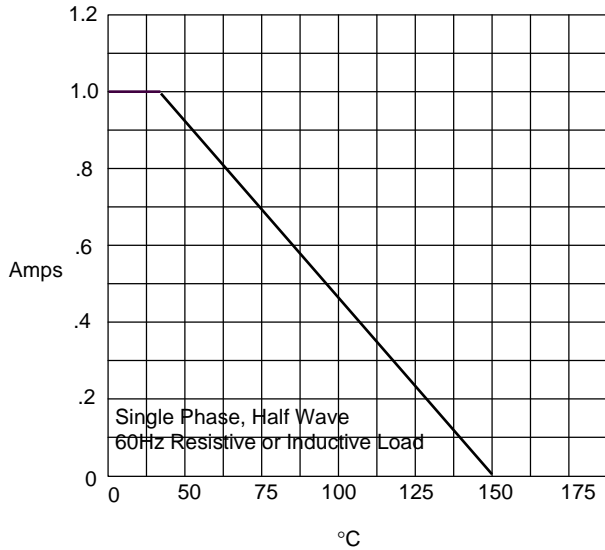
Instantaneous Forward Current - Amperes *versus* Instantaneous Forward Voltage - Volts

Figure 2
Typical Reverse Characteristics



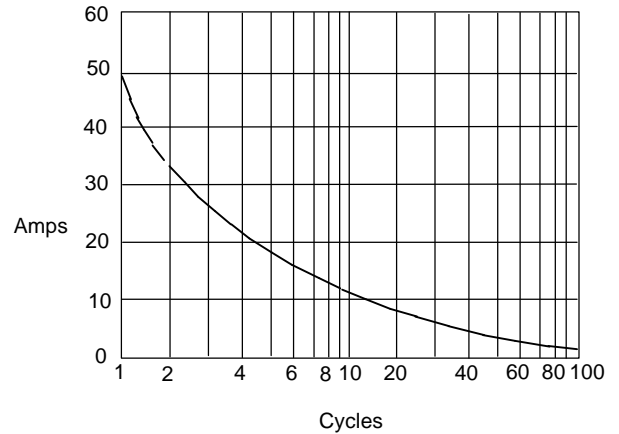
Instantaneous Reverse Leakage Current - MicroAmperes *versus* Percent Of Rated Peak Reverse Voltage - Volts

Figure 3
Forward Derating Curve



Average Forward Rectified Current - Amperes *versus* Ambient Temperature - °C

Figure 4
Peak Forward Surge Current



Peak Forward Surge Current - Amperes *versus* Number Of Cycles At 60Hz - Cycles